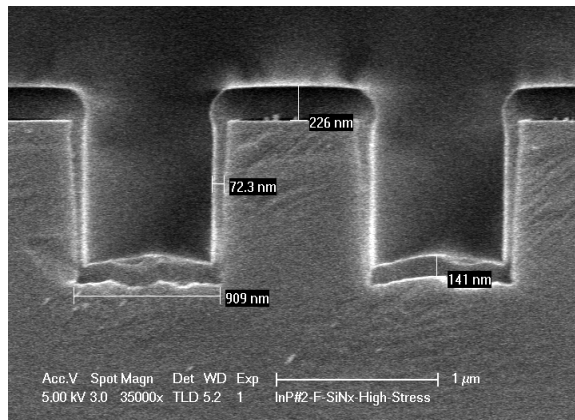
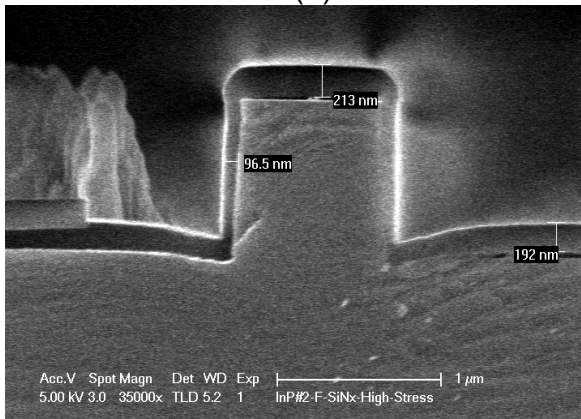


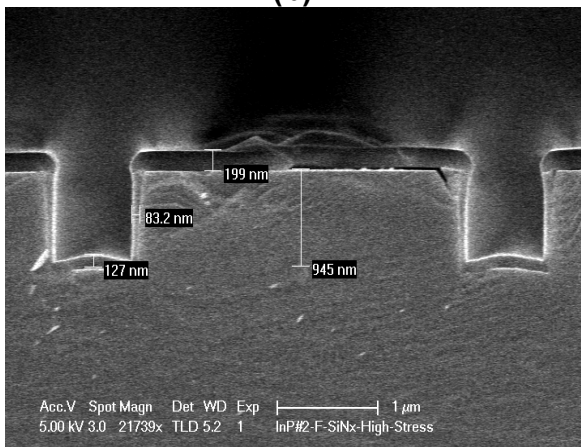
**Figure 2 (a)** (in a closed trench area), **(b)** (in an open area), and **(c)**. Sidewall coverage of SiNx film, deposited using Unaxis ICP tool (PM3) at 100 °C, with the chamber pressure=15 mT, bias/ICP powers=5/400 W, 2%SiH<sub>4</sub> (diluted in He)/N<sub>2</sub>/Ar=263/4/20 sccm, and deposition time=536 s [Sample's solvent clean and BHF dip (two minutes, to remove the remaining SiO<sub>2</sub> etch mask) were applied prior to the deposition].



(a)



(b)



(c)